



# BUK9M8R5-40H

N-channel 40 V, 8.5 mΩ logic level MOSFET in LFPAK33

29 January 2019

Product data sheet

## 1. General description

Automotive qualified logic level N-channel MOSFET in an LFPAK33 package using Trench 9 TrenchMOS technology. This product has been designed and qualified to AEC-Q101 for use in high performance automotive applications.

## 2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Trench 9 superjunction technology:
  - Low power losses, high power density
- LFPAK copper clip package technology:
  - High robustness and reliability
  - Gull wing leads for high manufacturability and AOI
- Repetitive avalanche rated

## 3. Applications

- 12 V automotive systems
- Powertrain, chassis, body and infotainment applications
- Medium/Low power motor drive
- DC-DC systems
- LED lighting

## 4. Quick reference data

Table 1. Quick reference data

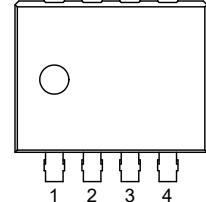
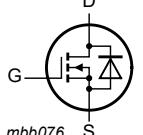
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25^{\circ}\text{C} \leq T_j \leq 175^{\circ}\text{C}$		-	-	40	V
$I_D$	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25^{\circ}\text{C}$ ; <a href="#">Fig. 2</a>	[1]	-	-	40	A
$P_{tot}$	total power dissipation	$T_{mb} = 25^{\circ}\text{C}$ ; <a href="#">Fig. 1</a>		-	-	59	W
<b>Static characteristics</b>							
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25^{\circ}\text{C}$ ; <a href="#">Fig. 11</a>		5	7.2	8.5	$\text{m}\Omega$
<b>Dynamic characteristics</b>							
$Q_{GD}$	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 4.5 \text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>		-	2.1	4.2	nC
<b>Source-drain diode</b>							
$Q_r$	recovered charge	$I_S = 15 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$		-	15	-	nC

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
S	softness factor	$I_S = 15 \text{ A}$ ; $dI_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 17</a>		-	0.61	-	

[1] 40A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	Mounting base; connected to drain	 LFPAK33 (SOT1210)	

## 6. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BUK9M8R5-40H	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210

## 7. Marking

**Table 4. Marking codes**

Type number	Marking code
BUK9M8R5-40H	98H040

## 8. Limiting values

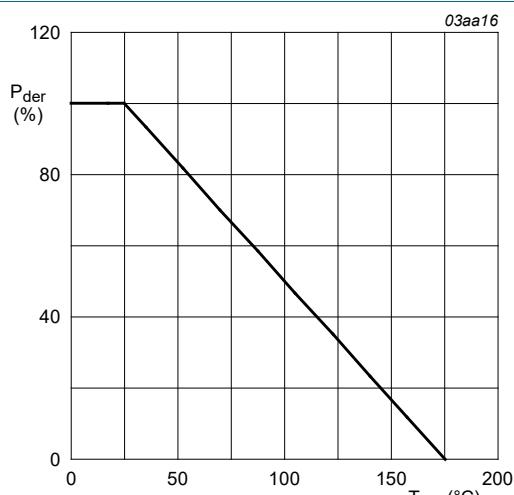
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$25 \text{ }^\circ\text{C} \leq T_j \leq 175 \text{ }^\circ\text{C}$		-	40	V
$V_{GS}$	gate-source voltage	DC; $T_j \leq 175 \text{ }^\circ\text{C}$		-10	16	V
$P_{tot}$	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a>		-	59	W
$I_D$	drain current	$V_{GS} = 10 \text{ V}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>	[1]	-	40	A
		$V_{GS} = 10 \text{ V}$ ; $T_{mb} = 100 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>		-	40	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10 \mu\text{s}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 3</a>		-	239	A
$T_{stg}$	storage temperature			-55	175	°C
$T_j$	junction temperature			-55	175	°C
<b>Source-drain diode</b>						

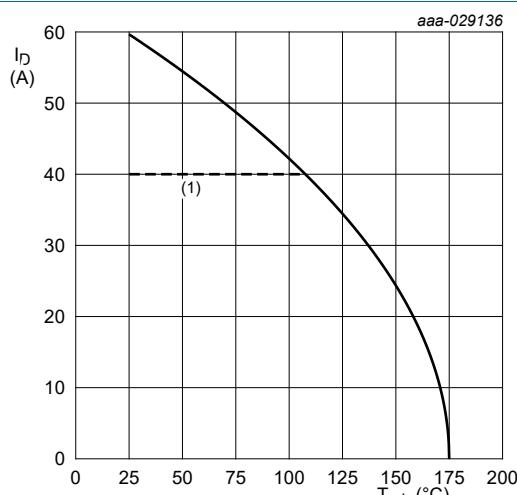
Symbol	Parameter	Conditions		Min	Max	Unit
$I_S$	source current	$T_{mb} = 25^\circ\text{C}$		-	40	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10 \mu\text{s}$ ; $T_{mb} = 25^\circ\text{C}$		-	239	A
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 40 \text{ A}$ ; $V_{sup} \leq 40 \text{ V}$ ; $R_{GS} = 50 \Omega$ ; $V_{GS} = 10 \text{ V}$ ; $T_{j(init)} = 25^\circ\text{C}$ ; unclamped; <a href="#">Fig. 4</a>	[2] [3]	-	24	mJ

[1] 40A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.  
 [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.  
 [3] Refer to application note AN10273 for further information.



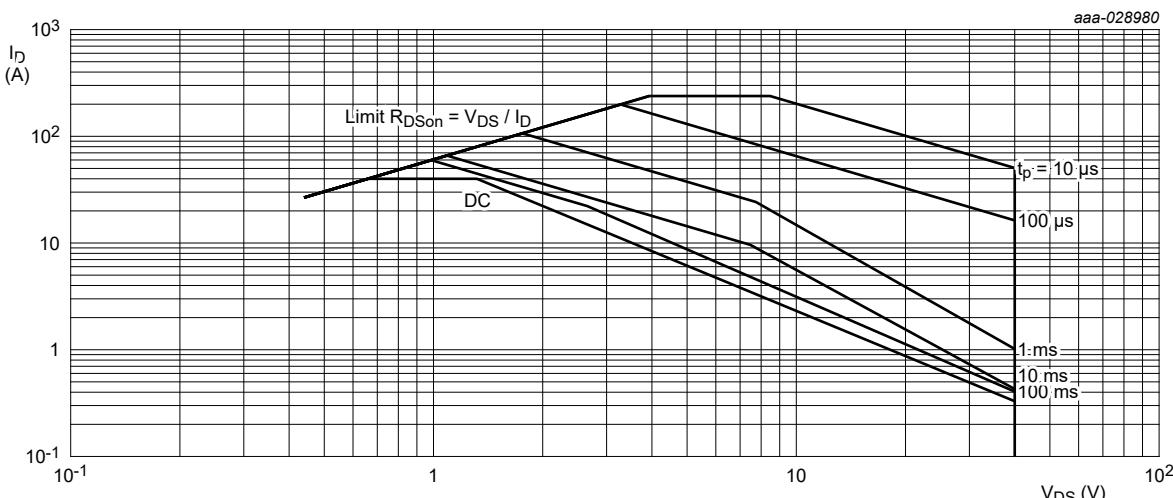
$$P_{der} = \frac{P_{tot}}{P_{tot}(25^\circ\text{C})} \times 100 \%$$

**Fig. 1. Normalized total power dissipation as a function of mounting base temperature**



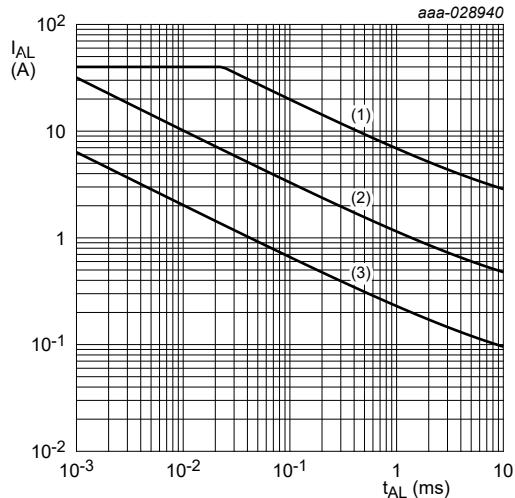
$V_{GS} \geq 10 \text{ V}$   
 (1) 40A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

**Fig. 2. Continuous drain current as a function of mounting base temperature**



$T_{mb} = 25^\circ\text{C}$ ;  $I_{DM}$  is a single pulse

**Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**



(1)  $T_j$  (init) = 25 °C; (2)  $T_j$  (init) = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 5</a>	-	2.33	2.56	K/W

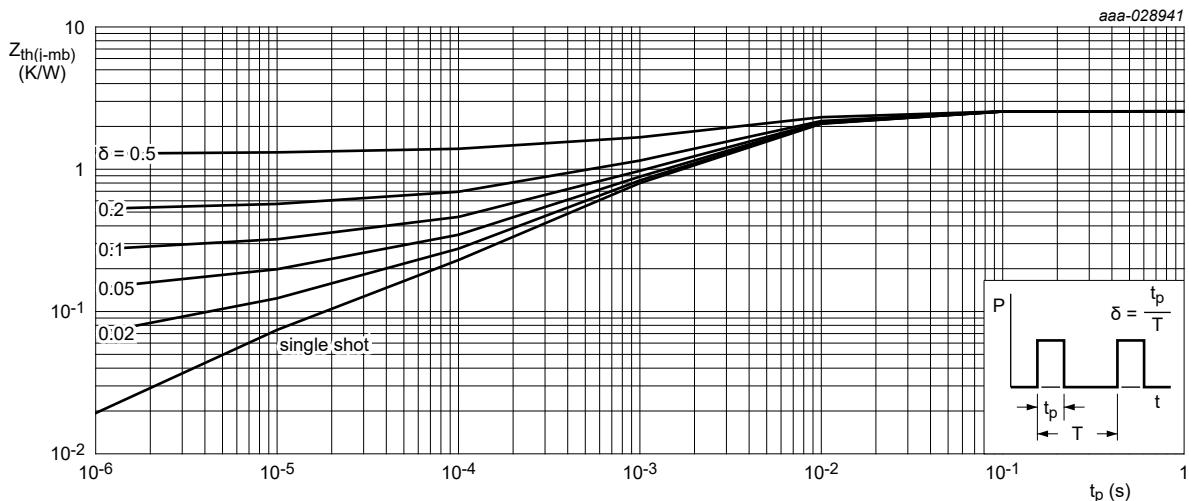


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 °C$	40	43	-	V

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55^\circ C$		36	40	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA; V_{DS}=V_{GS}; T_j = 25^\circ C$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>		1.45	1.77	2.15	V
		$I_D = 1 mA; V_{DS}=V_{GS}; T_j = -55^\circ C$ ; <a href="#">Fig. 10</a>		-	-	2.6	V
		$I_D = 1 mA; V_{DS}=V_{GS}; T_j = 175^\circ C$ ; <a href="#">Fig. 10</a>		0.7	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25^\circ C$		-	0.02	1	$\mu A$
		$V_{DS} = 16 V; V_{GS} = 0 V; T_j = 125^\circ C$		-	0.42	10	$\mu A$
		$V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175^\circ C$		-	30	500	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25^\circ C$		-	2	100	nA
		$V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25^\circ C$		-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 15 A; T_j = 25^\circ C$ ; <a href="#">Fig. 11</a>		5	7.2	8.5	$m\Omega$
		$V_{GS} = 10 V; I_D = 15 A; T_j = 105^\circ C$ ; <a href="#">Fig. 12</a>		6.8	10.2	12.8	$m\Omega$
		$V_{GS} = 10 V; I_D = 15 A; T_j = 125^\circ C$ ; <a href="#">Fig. 12</a>		7.5	11.1	13.7	$m\Omega$
		$V_{GS} = 10 V; I_D = 15 A; T_j = 175^\circ C$ ; <a href="#">Fig. 12</a>		9.1	13.5	16.5	$m\Omega$
		$V_{GS} = 4.5 V; I_D = 15 A; T_j = 25^\circ C$ ; <a href="#">Fig. 11</a>		6.3	9	11	$m\Omega$
		$V_{GS} = 4.5 V; I_D = 15 A; T_j = 105^\circ C$ ; <a href="#">Fig. 12</a>		8.6	12.7	16.5	$m\Omega$
		$V_{GS} = 4.5 V; I_D = 15 A; T_j = 125^\circ C$ ; <a href="#">Fig. 12</a>		9.5	13.8	17.7	$m\Omega$
		$V_{GS} = 4.5 V; I_D = 15 A; T_j = 175^\circ C$ ; <a href="#">Fig. 12</a>		11.5	16.7	21.4	$m\Omega$
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_j = 25^\circ C$		0.3	0.8	2	$\Omega$
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 15 A; V_{DS} = 20 V; V_{GS} = 10 V$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>		-	20	28	nC
		$I_D = 15 A; V_{DS} = 20 V; V_{GS} = 4.5 V$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>		-	9	13	nC
$Q_{GS}$	gate-source charge			-	3.6	5.4	nC
$Q_{GD}$	gate-drain charge			-	2.1	4.2	nC
$C_{iss}$	input capacitance	$V_{DS} = 25 V; V_{GS} = 0 V; f = 1 \text{ MHz}$ ; $T_j = 25^\circ C$ ; <a href="#">Fig. 15</a>		-	1286	1800	pF
$C_{oss}$	output capacitance			-	345	483	pF
$C_{rss}$	reverse transfer capacitance			-	49	108	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 20 V; R_L = 1.2 \Omega; V_{GS} = 4.5 V$ ; $R_{G(ext)} = 5 \Omega$		-	9.5	-	ns
$t_r$	rise time			-	9.4	-	ns
$t_{d(off)}$	turn-off delay time			-	11	-	ns
$t_f$	fall time			-	5.6	-	ns
<b>Source-drain diode</b>							
$V_{SD}$	source-drain voltage	$I_S = 15 A; V_{GS} = 0 V; T_j = 25^\circ C$ ; <a href="#">Fig. 16</a>		-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 15 A; dI_S/dt = -100 A/\mu s; V_{GS} = 0 V; V_{DS} = 20 V$ ; <a href="#">Fig. 17</a>		-	22	-	ns
$Q_r$	recovered charge	$I_S = 15 A; dI_S/dt = -100 A/\mu s; V_{GS} = 0 V; V_{DS} = 20 V$		-	15	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
S	softness factor	$I_S = 15 \text{ A}$ ; $dI_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 17</a>	-	0.61	-	
		$I_S = 15 \text{ A}$ ; $dI_S/dt = -500 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 17</a>	-	0.41	-	

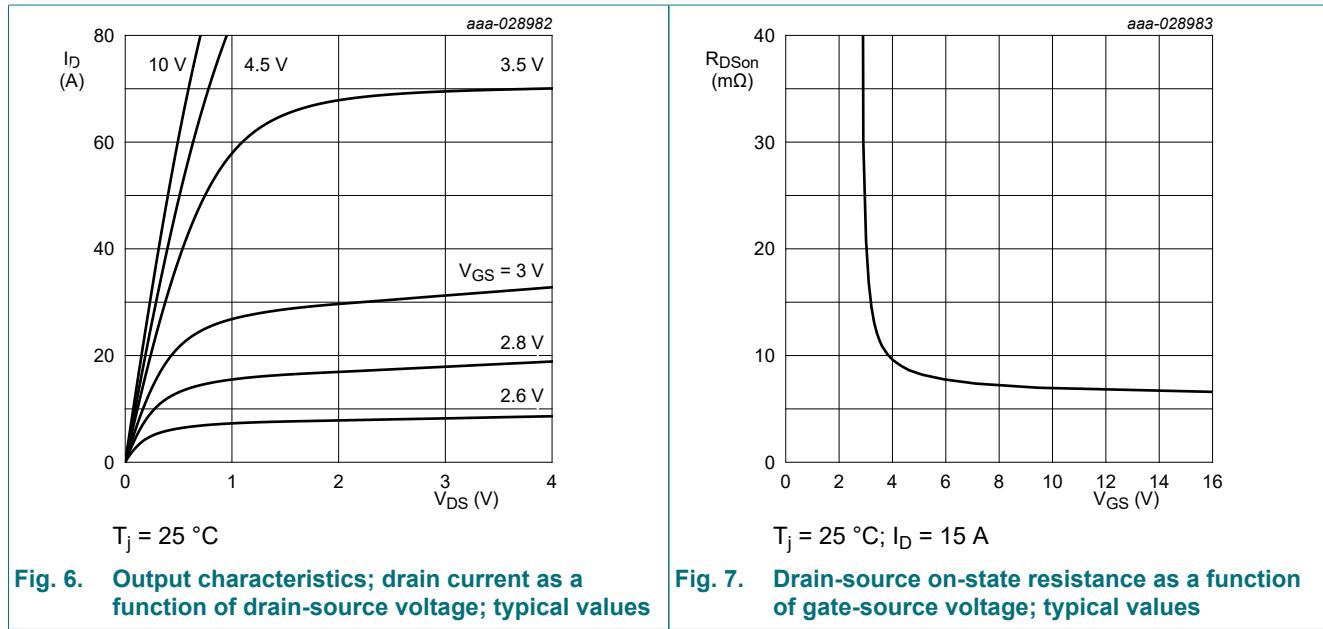


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

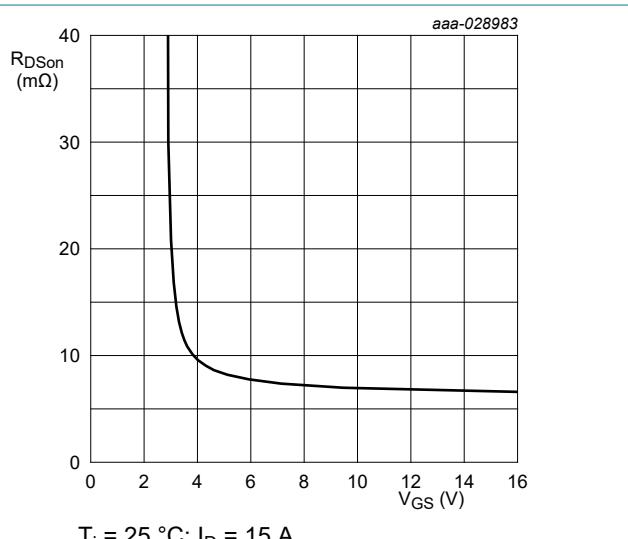


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

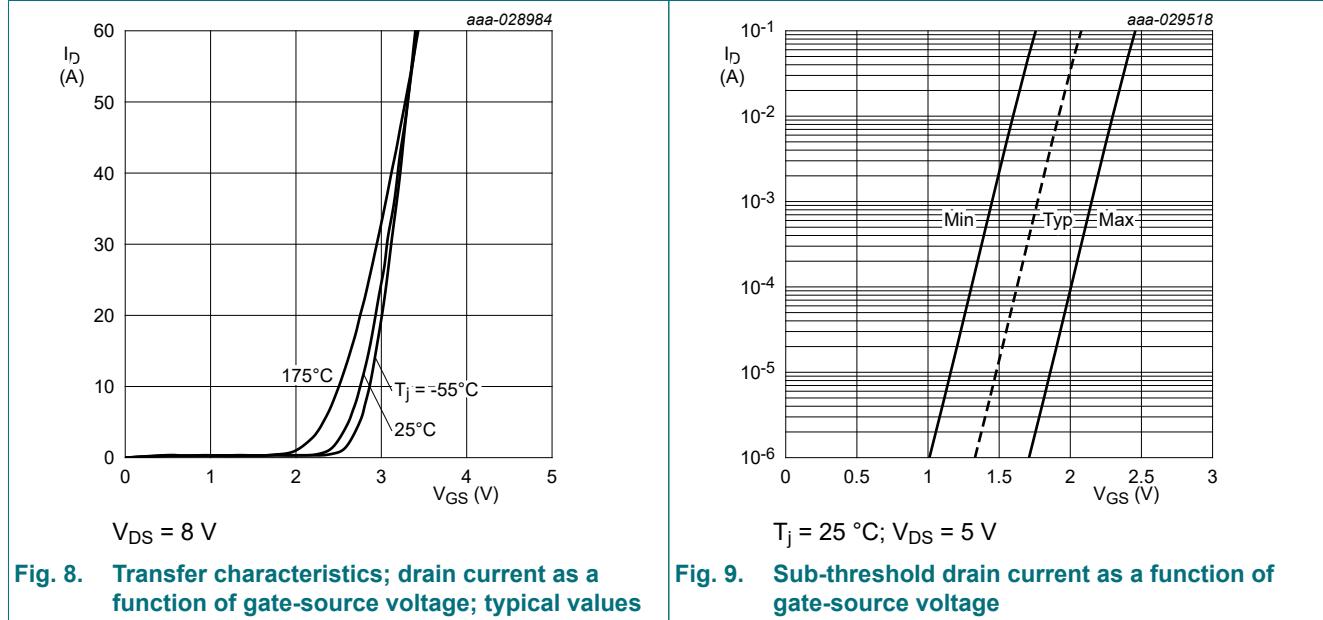


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

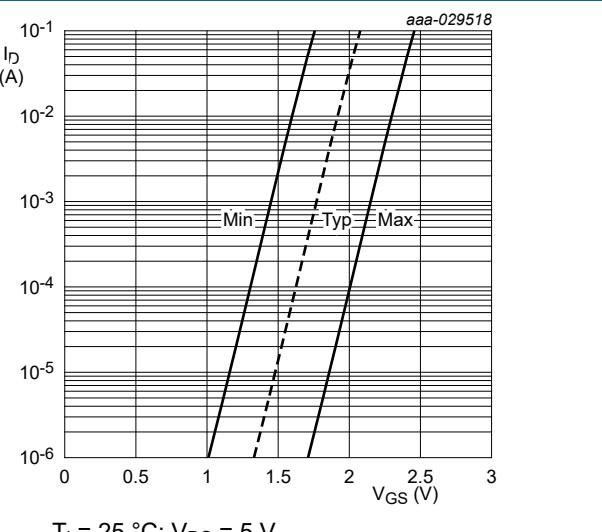


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

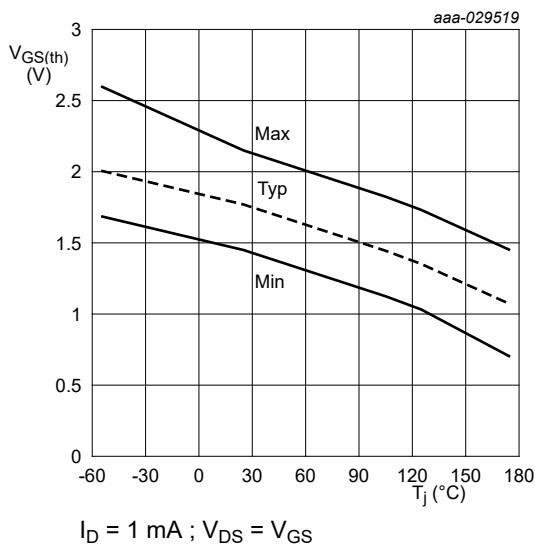


Fig. 10. Gate-source threshold voltage as a function of junction temperature

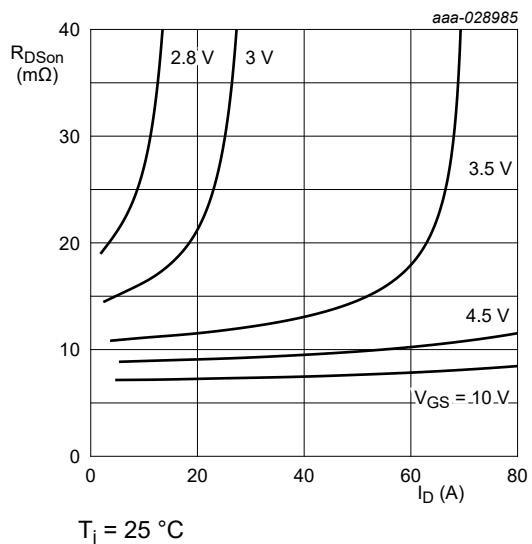
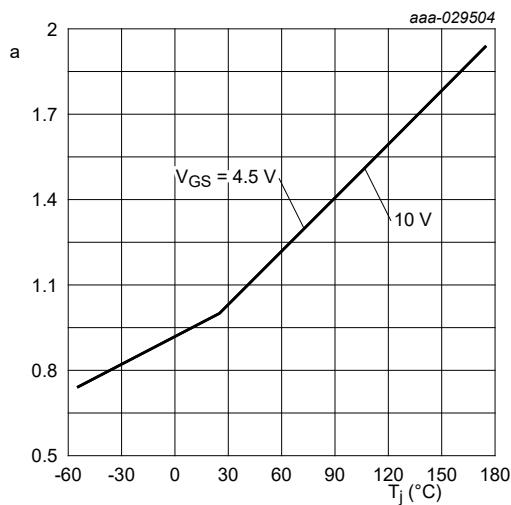


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

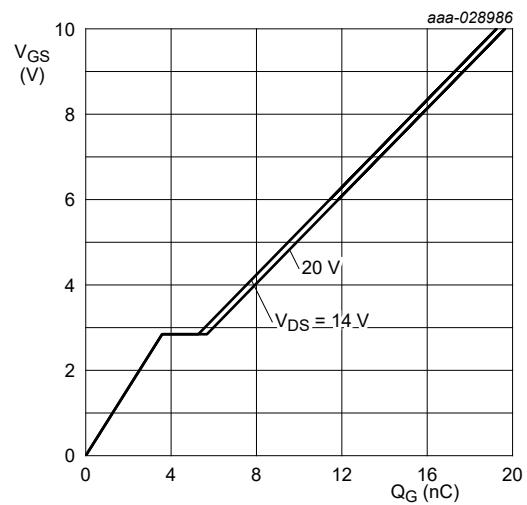


Fig. 13. Gate-source voltage as a function of gate charge; typical values

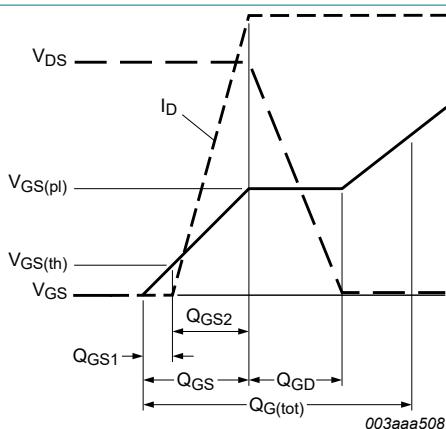


Fig. 14. Gate charge waveform definitions

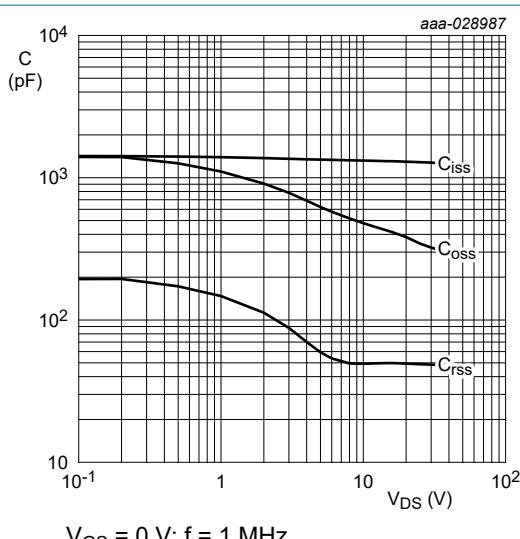


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

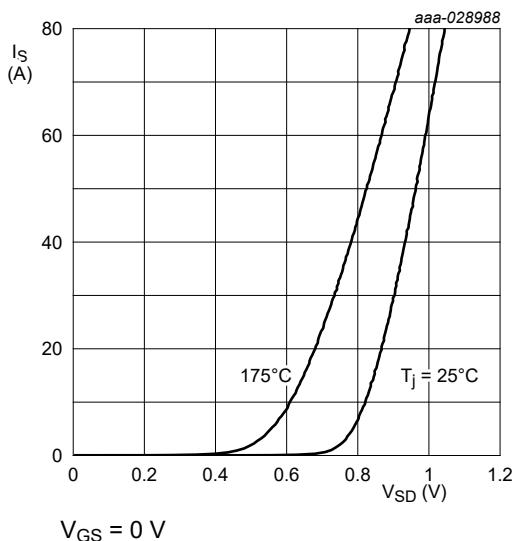


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

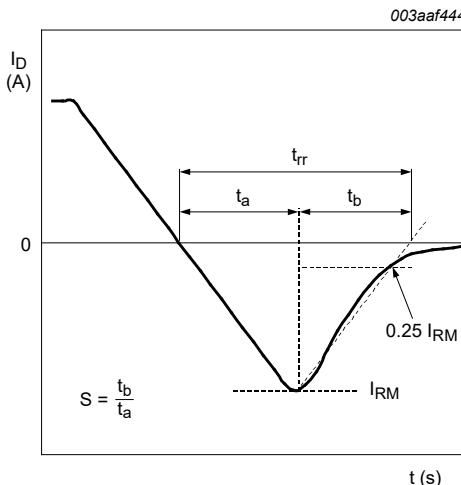
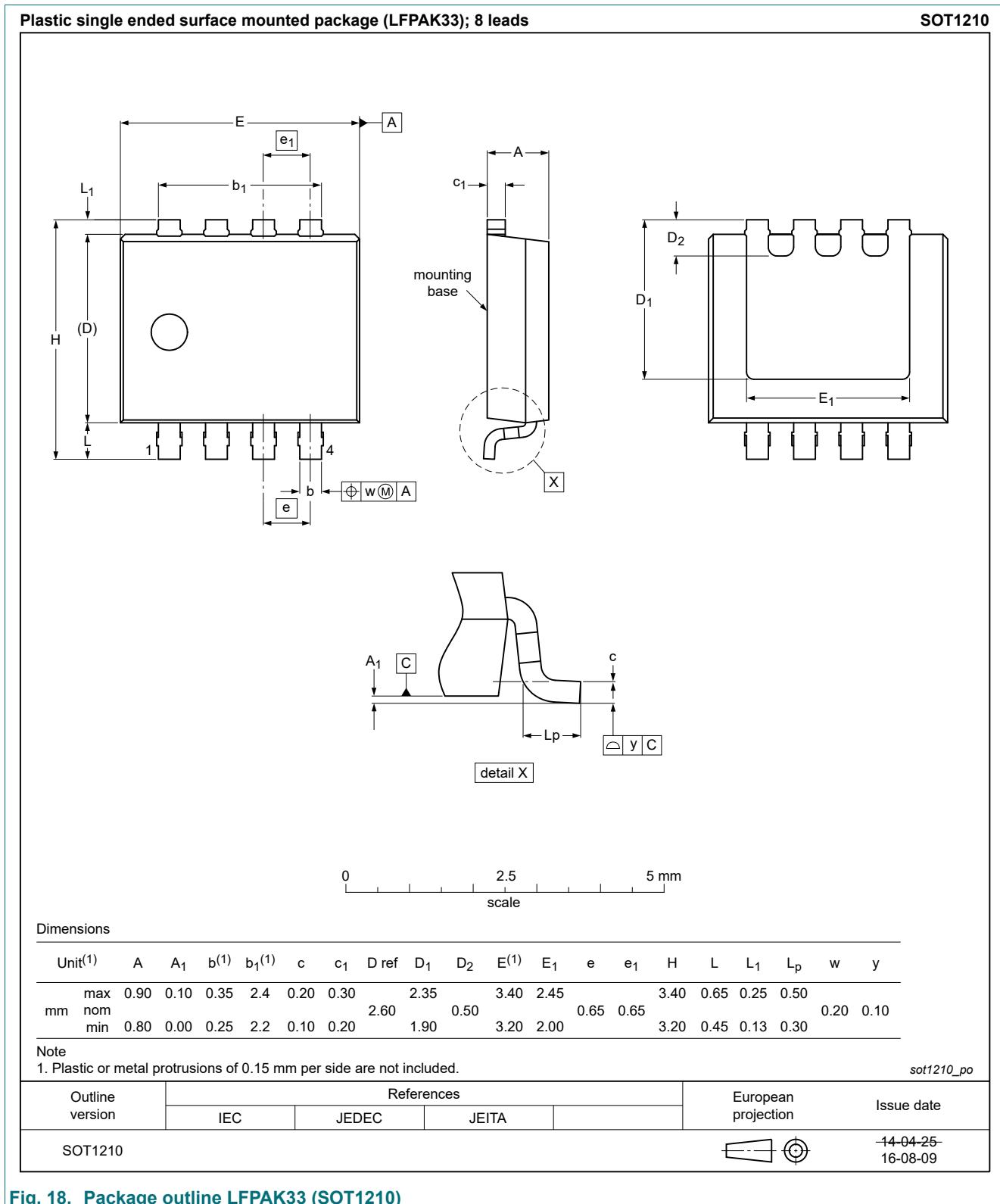


Fig. 17. Reverse recovery timing definition

## 11. Package outline



## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 29 January 2019

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